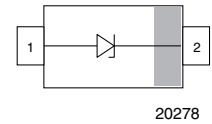
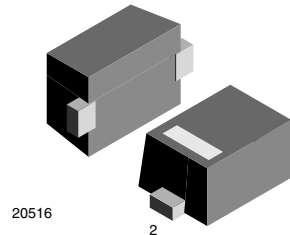


## ESD-Protection Diode in SOD923

### Features

- Single-line ESD-protection device
- ESD-immunity acc. IEC 61000-4-2
  - > 20 kV contact discharge
  - > 30 kV air discharge
- Tiny SOD923 package
- Package height = 0.4 mm
- Typ. capacitance 12 pF ( $V_R = 2.5\text{ V}$ ;  $f = 1\text{ MHz}$ )
- Leakage current  $< 0.1\ \mu\text{A}$  ( $V_R = 5\text{ V}$ )
- AEC Q101 qualified
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



### Marking (example only)



Bar = Cathode marking  
 X = Date code  
 Y = Type code (see table below)

### Ordering Information

| Device name   | Ordering code      | Taped units per reel<br>(8 mm tape on 7" reel) | Minimum order quantity |
|---------------|--------------------|--|------------------------|
| VESD05A1B-02Z | VESD05A1B-02Z-GS08 | 8000   | 8000                   |

### Package Data

| Device name   | Package name | Type code | Weight  | Molding compound flammability rating | Moisture sensitivity level        | Soldering conditions     |
|---------------|--------------|-----------|---------|--------------------------------------|-----------------------------------|--------------------------|
| VESD05A1B-02Z | SOD923       | H         | 0.45 mg | UL 94 V-0                            | MSL level 1 (according J-STD-020) | 260 °C/10 s at terminals |

### Absolute Maximum Ratings

| Rating                | Test condition   | Symbol    | Value         | Unit |
|-----------------------|--|-----------|---------------|------|
| Peak pulse current    | acc. IEC 61000-4-5, $t_p = 8/20\ \mu\text{s}$ /single shot | $I_{PPM}$ | 3             | A    |
| Peak pulse power      | acc. IEC 61000-4-5, $t_p = 8/20\ \mu\text{s}$ /single shot | $P_{PP}$  | 33            | W    |
| ESD immunity          | contact discharge acc. IEC 61000-4-2; 10 pulses            | $V_{ESD}$ | $\pm 20$      | kV   |
|                       | air discharge acc. IEC 61000-4-2; 10 pulses                | $V_{ESD}$ | $\pm 30$      | kV   |
| Operating temperature | Junction temperature                                       | $T_J$     | - 40 to + 125 | °C   |
| Storage temperature   |  | $T_{STG}$ | - 55 to + 150 | °C   |

\*\* Please see document "Vishay Green and Halogen-Free Definitions (5-2008)" <http://www.vishay.com/doc?99902>

## BiAs-Mode (Bidirectional Asymmetrical protection mode)

With the **VESD05A1B-02Z** one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified **Maximum Reverse Working Voltage** ( $V_{RWM}$ ) the protection diode between data line and ground offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the break through voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The **Clamping Voltage** ( $V_C$ ) is defined by the **Breakthrough Voltage** ( $V_{BR}$ ) level plus the voltage drop at the series impedance (resistance and inductance) of the protection device.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction of the protection diode. The low **Forward Voltage** ( $V_F$ ) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the **VESD05A1B-02Z** clamping behaviour is **Bidirectional** and **Asymmetrical (BiAs)**.



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## Electrical Characteristics

Ratings at 25 °C ambient temperature, unless otherwise specified

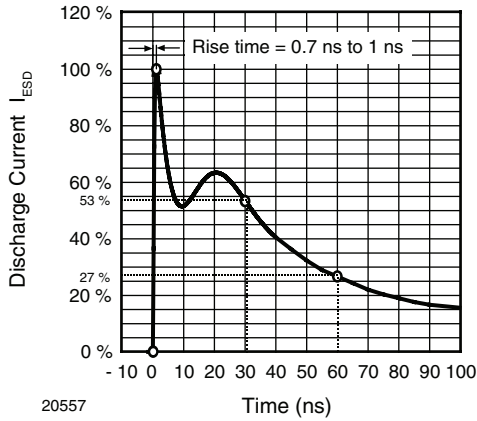
### VESD05A1B-02Z

BiAs mode (between pin 1 and pin 2)

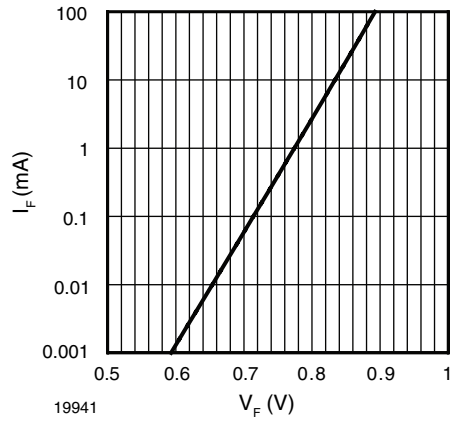
| Parameter                  | Test conditions/remarks                | Symbol      | Min. | Typ. | Max. | Unit    |
|----------------------------|--|-------------|------|------|------|---------|
| Protection paths           | number of lines which can be protected | $N_{lines}$ |      |      | 1    | lines   |
| Reverse stand off voltage  | at $I_R = 0.1 \mu A$                   | $V_{RWM}$   | 5    |      |      | V       |
| Reverse current            | at $V_R = 5 V$                         | $I_R$       |      | 0.01 | 0.1  | $\mu A$ |
| Reverse break down voltage | at $I_R = 1 mA$                        | $V_{BR}$    | 6    | 6.8  | 7.5  | V       |
| Reverse clamping voltage   | at $I_{PP} = 1 A$                      | $V_C$       |      | 8    | 9.5  | V       |
|                            | at $I_{PP} = I_{PPM} = 3 A$            | $V_C$       |      | 8.9  | 11   | V       |
| Forward clamping voltage   | at $I_{PP} = 0.2 A$                    | $V_F$       |      | 0.95 | 1.2  | V       |
|                            | at $I_{PP} = 1 A$                      | $V_F$       |      | 1.3  |      | V       |
|                            | at $I_{PP} = I_{PPM} = 3 A$            | $V_F$       |      | 1.9  |      | V       |
| Capacitance                | at $V_R = 0 V$ ; $f = 1 MHz$           | $C_D$       |      | 19   | 23   | pF      |
|                            | at $V_R = 2.5 V$ ; $f = 1 MHz$         | $C_D$       |      | 12   |      | pF      |

## Typical Characteristics

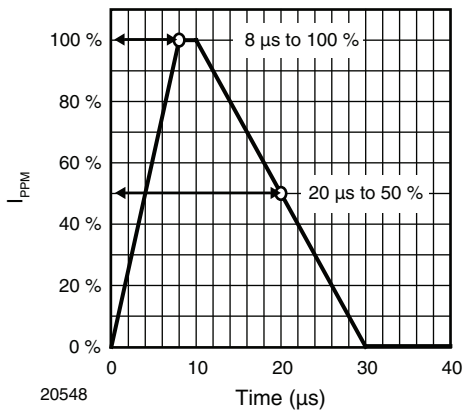
$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified



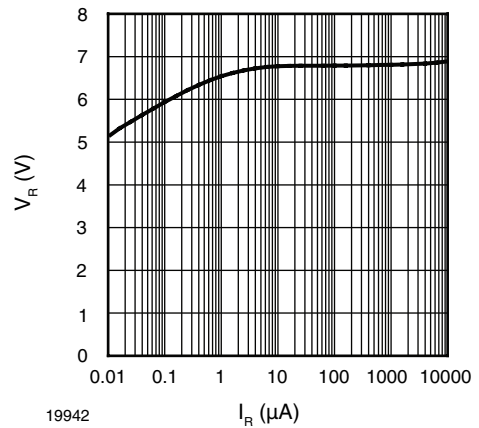
20557  
Figure 1. ESD Discharge Current Wave Form acc. IEC 61000-4-2 (330  $\Omega$ /150 pF)



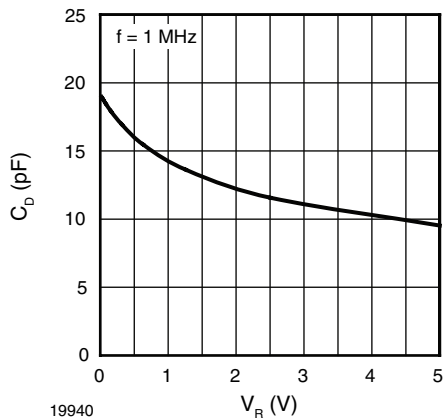
19941  
Figure 4. Typical Forward Current  $I_F$  vs. Forward Voltage  $V_F$



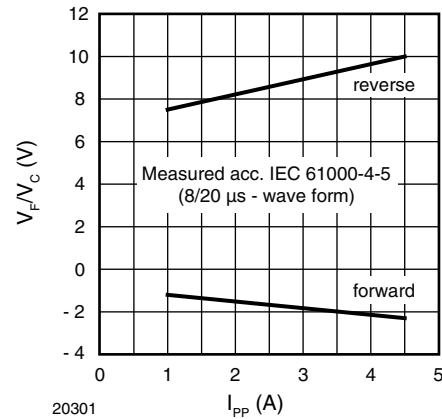
20548  
Figure 2. 8/20  $\mu\text{s}$  Peak Pulse Current Wave Form acc. IEC 61000-4-5



19942  
Figure 5. Typical Reverse Voltage  $V_R$  vs. Reverse Current  $I_R$



19940  
Figure 3. Typical Capacitance  $C_D$  vs. Reverse Voltage  $V_R$



20301  
Figure 6. Typical Clamping Voltage vs. Peak Pulse Current  $I_{PP}$

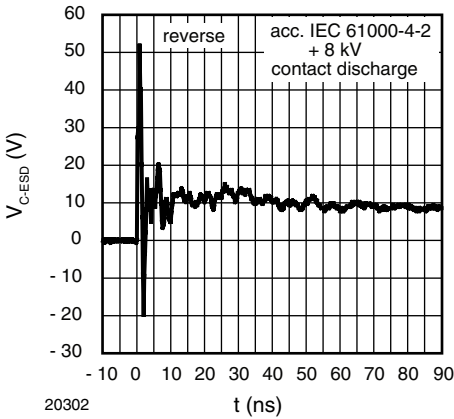


Figure 7. Typical Clamping Performance at + 8 kV Contact Discharge (acc. IEC 61000-4-2)

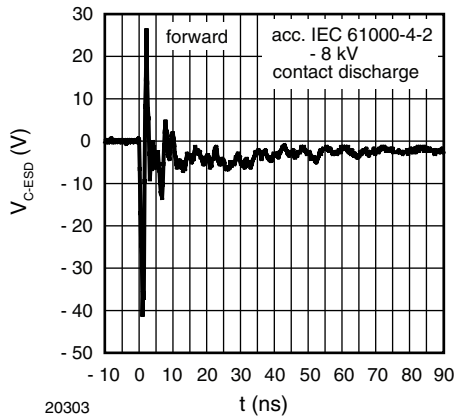


Figure 8. Typical Clamping Performance at - 8 kV Contact Discharge (acc. IEC 61000-4-2)

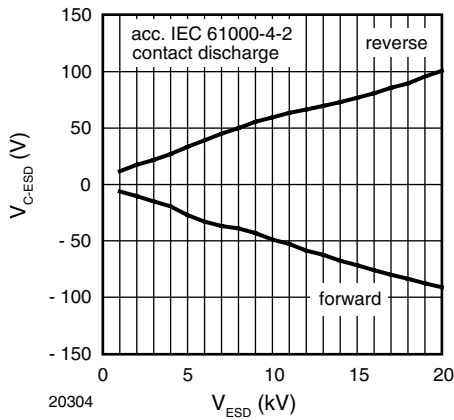
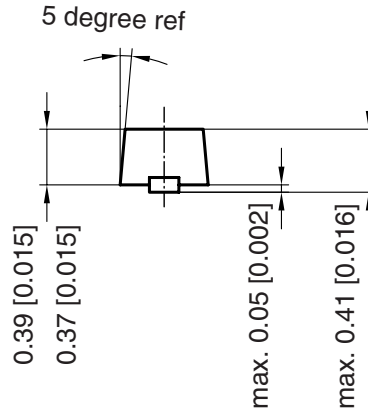
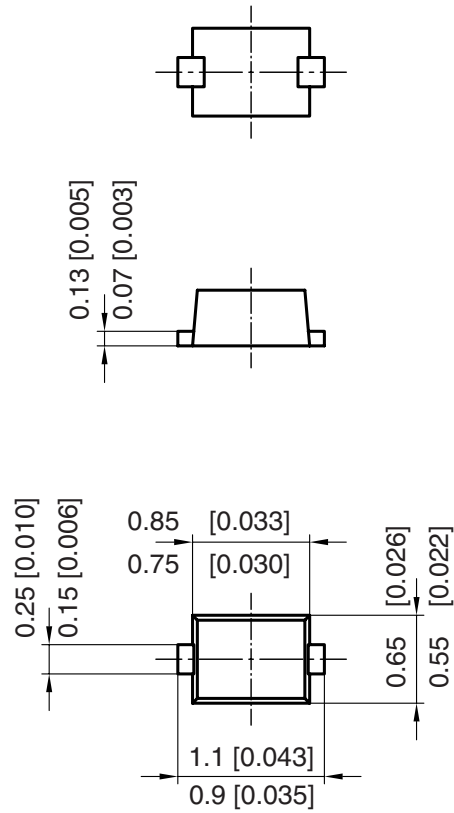
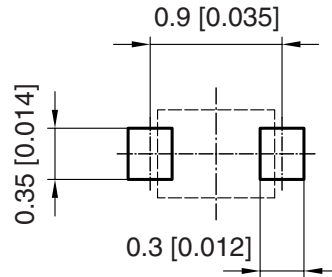


Figure 9. Typical Clamping Voltage at ± ESD Contact Discharge (acc. IEC 61000-4-2)

**Package Dimensions** in millimeters (inches): **SOD923**



foot print recommendation:



Document no.: S8-V-3880.05-001 (4)

Rev. 1 - Date: 05.July.2006

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### Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design  
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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